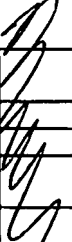


PTO/SB/08a/b (08-03)
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		Application Number	10/509,354		
		Filing Date	September 27, 2004		
		First Named Inventor	Nick Zakhleniuk		
		Art Unit	N/A		
		Examiner Name	Not Yet Assigned		
Sheet	1	of	2	Attorney Docket Number	BTW-087US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	A1	4,720,835	01-19-1988	Yukitoshi, <i>et al.</i>	
	A2	5,187,715	02-16-1993	Weisbuch, <i>et al.</i>	
	A3	5,604,762	02-18-1997	Morinaga, <i>et al.</i>	
	A4	5,732,102A	03-24-1998	Bouadma	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
	A8	EP 0300790 B1	01-25-1989	Kokusai Denshin Denwa Co. Ltd.		
	A9	EP 0467781 A2	01-22-1992	Kokusai Denshin Denwa Co. Ltd.		
	A10	EP 0546706 A1	03-13-1996	AT&T Corp.		
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	A13	GB 2306773 A	05-07-1997	Toshiba Cambridge Research Centre Limited		
	A14	JP 01223791 A	09-06-1989	Fujitsu Ltd.		
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	A16	JP 09222588 A	08-26-1997	Fujitsu Ltd.		
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NON PATENT LITERATURE DOCUMENTS			
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	A18	Aizawa, T., <i>et al.</i> "Observation of Field-Induced Refractive Index Variation in Quantum Box Structure." <i>IEEE Photonics Technology Letters</i> . 1991 Oct 1. 3(10):907-9.	

Examiner Signature		Date Considered	7/07
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/509,354
				Filing Date	September 27, 2004
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				Art Unit	N/A
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Sheet	2	of	2	Attorney Docket Number	BTW-087US

NON PATENT LITERATURE DOCUMENTS			
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	B1	Allen, C.N., et al. "InAs Self-Assembled Quantum-Dot Lasers Grown on (100) InP." <i>Applied Physics Letters</i> . 2002 May 13. 80(19): 3629-31.	
	B2	Bimberg, D., et al. "InGaAs-GaAs Quantum-Dot Lasers." <i>IEEE Journal of Selected Topics in Quantum Electronics</i> . 1997 Apr. 3(2).	
	B3	Delorme, F., et al. "Ultra-Fast Optical Switching Operation of DBR Lasers Using an Electro-Optical Tuning Section." <i>IEEE Photonics Technology Letters</i> , 1995 Mar. 7(3).	
	B4	Griesinger, U.A., et al. "Realization of Dot DFB Lasers." <i>IEEE Photonics Technology Letters</i> . 1996 May 1. 8(5): 587-9.	
	B5	Heinrichsdorff, F., et al. "Room-Temperature Continuous-Wave Lasing from Stacked InAs/GaAs Quantum Dots Grown by Metalorganic Chemical Vapor Deposition." <i>Applied Physics Letters</i> . 1997 Jul 7. 71(1): 22-4.	
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	B7	Kirstaedter, N., et al. "Low Threshold, Large T Injection Laser Emission From (InGa) As Quantum Dots." <i>Electronics Letters</i> . 1994 Aug 18. 30(17):1416-7.	
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	B9	Lee, S.S., et al. "Analysis and Design of High-Speed High-Efficiency GaAs-AlGaAs Double-Heterostructure Waveguide Phase Modulator." <i>IEEE Journal of Quantum Electronics</i> . 1991 Mar. 27(3).	
	B10	Lester, L.F., et al. "Optical Characteristics of 1.24-μm InAs Quantum-Dot Laser Diodes." <i>IEEE Photonics Technology Letters</i> . 1999 Aug. 11(8): 931-3.	
	B11	Murata, S., et al. "Spectral Characteristics for a 1.5 μm DBR Laser with Frequency-Tuning Region." <i>IEEE Journal of Quantum Electronics</i> . 1987 Jun 1. QE-23(6):835-8.	
	B12	Oshinowo, J., et al. "Highly Uniform InGaAs/GaAs Quantum Dots (-15 NM) by Metalorganic Chemical Vapor Deposition." <i>Applied Physics Letters</i> . 1994 Sep 12. 765(11):1421-3.	
	B13	Ravikumar, K.G., et al. "Analysis of Electric Field Effect in Quantum Box Structure and Its Application to Low-Loss Intersectional Type Optical Switch." <i>Journal of Lightwave Technology</i> . 1991 Oct 1. 9(10):1376-85.	
	B14	Walker, R.G. "High-Speed III-V Semiconductor Intensity Modulators." <i>IEEE Journal of Quantum Electronics</i> . 1991 Mar 1. 27(3):654-67.	

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